Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

MSA-0436
Cascadable Silicon Bipolar MMIC Amplifiers

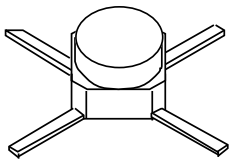
Data Sheet

Description
The MSA-0436 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a cost effective, microstrip package. This MMIC is designed for use as a general purpose 50Ω gain block. Typical applications include narrow and broad band IF and RF amplifiers in industrial and military applications.

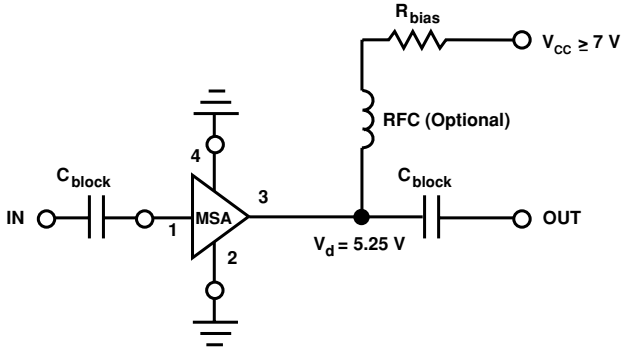
The MSA-series is fabricated using Avago's 10 GHz f_T, 25 GHz f_{MAX}, silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

Features
- Cascadable 50Ω Gain Block
- 3 dB Bandwidth: DC to 3.8 GHz
- 12.5 dBm Typical $P_{1\,dB}$ at 1.0 GHz
- 8.5 dB Typical Gain at 1.0 GHz
- Unconditionally Stable (k>1)
- Cost Effective Ceramic Microstrip Package

36 micro-X Package



Typical Biasing Configuration



MSA-0436 Absolute Maximum Ratings

Parameter	Absolute Maximum[1]
Device Current	100 mA
Power Dissipation[2,3]	650 mW
RF Input Power	+13 dBm
Junction Temperature	150°C
Storage Temperature[4]	–65 to 150°C

Thermal Resistance[2,5]:
θ_{jc} = 140°C/W

Notes:
1. Permanent damage may occur if any of these limits are exceeded.
2. T_{CASE} = 25°C.
3. Derate at 7.1 mW/°C for T_C > 109°C.
4. Storage above +150°C may tarnish the leads of this package making it difficult to solder into a circuit.
5. The small spot size of this technique results in a higher, though more accurate determination of q_{jc} than do alternate methods.

Electrical Specifications[1], T_A = 25°C

Symbol	Parameters and Test Conditions: I_d = 50 mA, Z_O = 50 Ω		Units	Min.	Typ.	Max.
G_P	Power Gain ($\|S_{21}\|^2$)	f = 0.1 GHz	dB	7.5	8.5	9.5
ΔG_P	Gain Flatness	f = 0.1 to 2.5 GHz	dB		±0.6	±1.0
$f_{3\ dB}$	3 dB Bandwidth		GHz		3.8	
VSWR	Input VSWR	f = 0.1 to 2.5 GHz			1.4:1	
	Output VSWR	f = 0.1 to 2.5 GHz			1.9:1	
NF	50 Ω Noise Figure	f = 1.0 GHz	dB		6.5	
$P_{1\ dB}$	Output Power at 1 dB Gain Compression	f = 1.0 GHz	dBm		12.5	
IP_3	Third Order Intercept Point	f = 1.0 GHz	dBm		25.5	
t_D	Group Delay	f = 1.0 GHz	psec		125	
V_d	Device Voltage		V	4.75	5.25	5.75
dV/dT	Device Voltage Temperature Coefficient		mV/°C		–8.0	

Note:
1. The recommended operating current range for this device is 30 to 70 mA. Typical performance as a function of current is on the following page.

Ordering Information

Part Numbers	No. of Devices	Comments
MSA-0436-BLKG	100	Bulk
MSA-0436-TR1G	1000	7" Reel

MSA-0436 Typical Scattering Parameters (Z_0 = 50 Ω, T_A = 25°C, I_d = 50 mA)

Freq. GHz	S_{11}		S_{21}			S_{12}			S_{22}	
	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang
0.1	.08	175	8.5	2.67	175	–16.4	.151	1	.20	–10
0.2	.08	172	8.5	2.68	170	–16.3	.153	2	.20	–16
0.4	.07	171	8.5	2.67	161	–16.4	.151	3	.20	–33
0.6	.07	166	8.5	2.66	151	–16.2	.155	6	.21	–45
0.8	.05	169	8.4	2.64	142	–16.1	.156	8	.22	–57
1.0	.05	175	8.3	2.61	136	–16.0	.159	10	.24	–68
1.5	.04	–142	8.1	2.55	109	–15.0	.178	13	.26	–96
2.0	.09	–145	7.8	2.46	87	–14.2	.196	15	.28	–123
2.5	.14	–154	7.3	2.33	71	–13.1	.221	18	.31	–140
3.0	.22	–175	6.6	2.14	50	–12.5	.238	14	.33	–160
3.5	.28	170	5.8	1.94	32	–11.7	.260	9	.35	–173
4.0	.34	156	4.8	1.74	15	–11.3	.271	4	.34	–179
4.5	.37	140	3.9	1.57	–1	–10.7	.291	–2	.33	–171
5.0	.42	120	3.0	1.41	–16	–10.4	.302	–8	.32	–160

Typical Performance, T_A = 25°C

(unless otherwise noted)

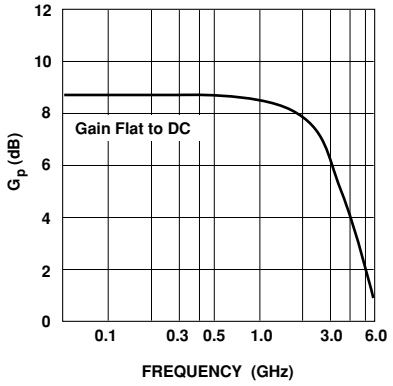


Figure 1. Typical Power Gain vs. Frequency, T_A = 25°C, I_d = 50 mA.

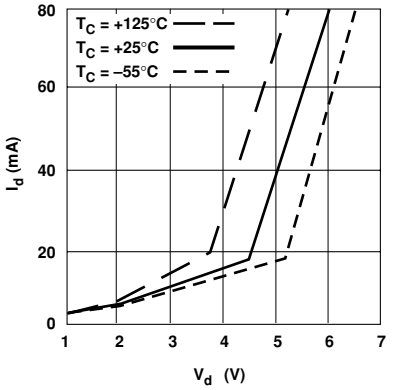


Figure 2. Device Current vs. Voltage.

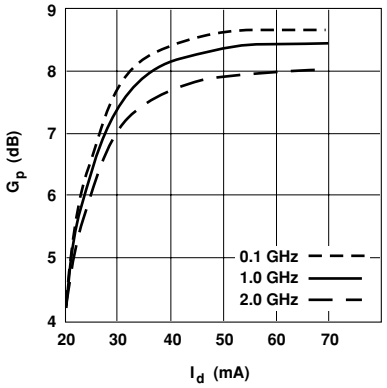


Figure 3. Power Gain vs. Current.

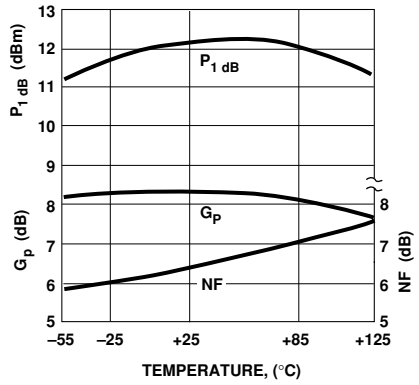


Figure 4. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature, f = 1.0 GHz, I_d = 50 mA.

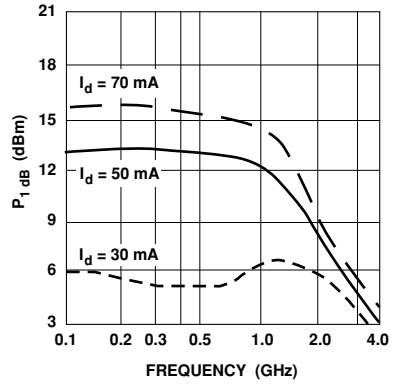


Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.

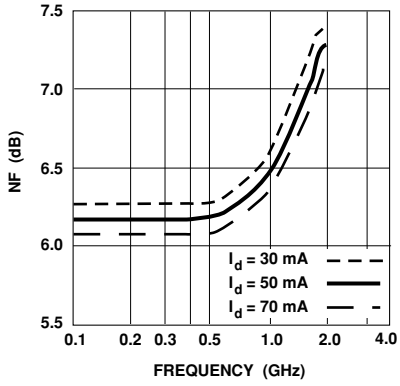
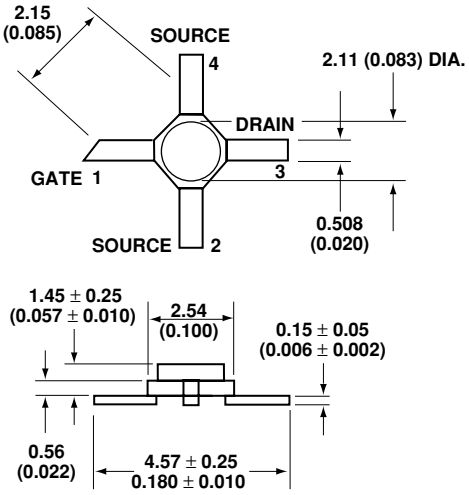


Figure 6. Noise Figure vs. Frequency.

36 micro-X Package Dimensions



Notes:
1. **Dimensions are in millimeters (inches)**
2. **Tolerances: in .xxx = ± 0.005**
   mm .xx = ± 0.13

For product information and a complete list of distributors, please go to our web site: **www.avagotech.com**

AV02-0303EN - April 12, 2007